8-Bit Latched Transceiver

Features

- Function and pinout compatible with FCT and F logic
- FCT-C speed at 5.3 ns max. (Com'l) FCT-A speed at 6.5 ns max. (Com'l)
- 25W output series resistors to reduce transmission line reflection noise
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- Sink current 12 mA (Com'l), 12 mA (Mil)
  Source current 15 mA (Com'l), 12 mA (Mil)
- Separation controls for data flow in each direction
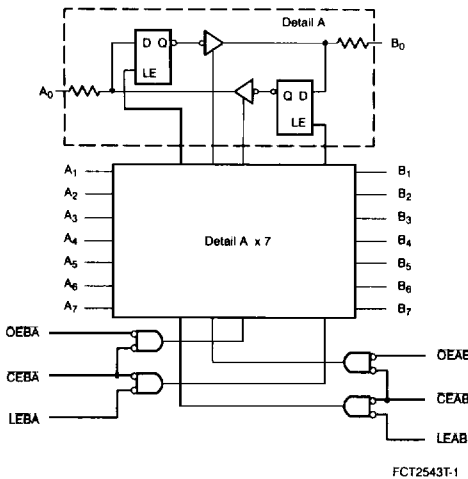- Back to back latches for storage
- ESD > 2000V

Functional Description

The FCT2543T Octal Latched Tranceiver contains two sets of eight D-type latches. Separate Latch Enable ($\overline{LEAB}$, $\overline{LEBA}$) and Output Enable ($\overline{OEAB}$, $\overline{OEBA}$) permits each latch set to have independent control of inputting and outputting in either direction of data flow. For data flow from A to B, for example, the A-to-B Enable ($\overline{CEAB}$) input must be LOW to enter data from A or to take data from B, as indicated in the truth table. With $\overline{CEAB}$ LOW, a LOW signal on the A-to-B Latch Enable ($\o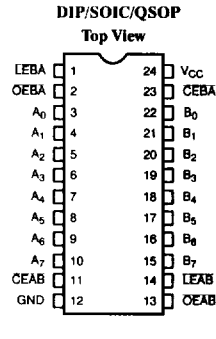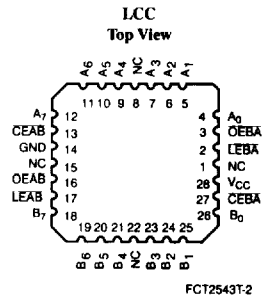verline{LEAB}$) input makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the $\overline{LEAB}$ signal puts the A latches in the storage mode and their output no longer change with the A inputs. With $\overline{CEAB}$ and $\overline{OEAB}$ both LOW, the three-state B output buffers are active and reflect data present at the output of the A latches. Control of data from B to A is similar, but uses $\overline{CEAB}$, $\overline{LEAB}$, and $\overline{OEAB}$ inputs. On-chip termination resistors have been added to the outputs to reduce system noise caused by reflections. The FCT2543T can be used to replace the FCT543T to reduce noise in an existing design.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

Functional Block Diagram

Pin Configurations

FCT2543T-2

FCT2543T-1

FCT2543T-3

Pin Description

Name	Description
$\overline{OEAB}$	A-to-B Output Enable Input (Active LOW)
$\overline{OEBA}$	B-to-A Output Enable Input (Active LOW)
$\overline{CEAB}$	A-to-B Enable Input (Active LOW)
$\overline{CEBA}$	B-to-A Enable Input (Active LOW)
$\overline{LEAB}$	A-to-B Latch Enable Input (Active LOW)
$\overline{LEBA}$	B-to-A Latch Enable Input (Active LOW)
A	A-to-B Data Inputs or B-to-A Three-State Outputs
B	B-to-A Data Inputs or A-to-B Three-State Outputs

Function Table[1,2]

Inputs			Latch	Outputs
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A-to-B[3]	B
H	X	X	Storing	High Z
X	H	X	Storing	X
X	X	H	X	High Z
L	L	L	Transparent	Current A Inputs
L	H	L	Storing	Previous A Inputs

Maximum Ratings[4, 5]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .... $-65°C$ to $+150°C$

Ambient Temperature with
Power Applied .... $-65°C$ to $+135°C$

Supply Voltage to Ground Potential .... $-0.5V$ to $+7.0V$

DC Input Voltage .... $-0.5V$ to $+7.0V$

DC Output Voltage .... $-0.5V$ to $+7.0V$

DC Output Current (Maximum Sink Current/Pin) .... 120 mA

Power Dissipation 0.5W

Notes:
1. H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care.
2. A-to-B data flow shown; B-to-A is the same, except using $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
3. Before $\overline{LEAB}$ LOW-to-HIGH transition.
4. Unless otherwise noted, these limits are over the operating free-air temperature range.

Static Discharge Voltage .... $>2001V$
(per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V_{CC}
Commercial	CT, DT	$0°C$ to $+70°C$	$5V \pm 5\%$
Commercial	T, AT	$-40°C$ to $+85°C$	$5V \pm 5\%$
Military[6]	All	$-55°C$ to $+125°C$	$5V \pm 10\%$

5. Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
6. T_A is the "instant on" case temperature.

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Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		Min.	Typ.[7]	Max.	Unit
V_{OH}	Output HIGH Voltage	$V_{CC}=Min., I_{OH}=-15$ mA	Com'l	2.4	3.3		V
		$V_{CC}=Min., I_{OH}=-12$ mA	Mil	2.4	3.3		V
V_{OL}	Output LOW Voltage	$V_{CC}=Min., I_{OL}=12$ mA	Com'l		0.3	0.55	V
		$V_{CC}=Min., I_{OL}=12$ mA	Mil		0.3	0.55	V
R_{OUT}	Output Resistance	$V_{CC}=Min., I_{OL}=12$ mA	Com'l	20	25	40	Ω
		$V_{CC}=Min., I_{OL}=12$ mA	Mil		25		Ω
V_{IH}	Input HIGH Voltage			2.0			V
V_{IL}	Input LOW Voltage					0.8	V
V_H	Hysteresis[8]	All inputs			0.2		V
V_{IK}	Input Clamp Diode Voltage	$V_{CC}=Min., I_{IN}=-18$ mA			−0.7	−1.2	V
I_{IH}	Input HIGH Current	$V_{CC}=Max., V_{IN}=V_{CC}$				5	μA
I_{IH}	Input HIGH Current	$V_{CC}=Max., V_{IN}=2.7V$				±1	μA
I_{IL}	Input LOW Current	$V_{CC}=Max., V_{IN}=0.5V$				±1	μA
I_{OZH}	Off State HIGH-Level Output Current	$V_{CC}=Max., V_{OUT}=2.7V$				15	μA
I_{OZL}	Off State LOW-Level Output Current	$V_{CC}=Max., V_{OUT}=0.5V$				−15	μA
I_{OS}	Output Short Circuit Current[9]	$V_{CC}=Max., V_{OUT}=0.0V$		−60	−120	−225	mA
I_{OFF}	Power-Off Disable	$V_{CC}=0V, V_{OUT}=4.5V$				±1	μA

Capacitance[8]

Parameter	Description	Test Conditions	Typ. [7]	Max.	Unit
C_{IN}	Input Capacitance		5	10	pF
C_{OUT}	Output Capacitance		9	12	pF

Notes:
7. Typical values are at $V_{CC}=5.0V$, $T_A=+25°C$ ambient.
8. This parameter is guaranteed but not tested.
9. Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametrics tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ.[7]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	V_{CC}=Max., $V_{IN} \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$	0.1	0.2	mA
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	V_{CC}=Max., V_{IN}=3.4V,[10] f_1=0, Outputs Open	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current[11]	V_{CC}=Max., One Input Toggling, 50% Duty Cycle, Outputs Open, $\overline{CEAB}$ and $\overline{OEAB}$=LOW, $\overline{CEBA}$=HIGH, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC}-0.2V$	0.06	1.2	mA/MHz
I_C	Total Power Supply Current[12]	V_{CC}=Max., f_0=10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f_1=5 MHz, $\overline{CEAB}$ and $\overline{OEAB}$=LOW, $\overline{CEBA}$=HIGH, $f_0=\overline{LEAB}$ =10 MHz, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC}-0.2V$	0.7	1.4	mA
		V_{CC}=Max., f_0=10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f_1=5 MHz, $\overline{CEAB}$ and $\overline{OEAB}$=LOW, $\overline{CEBA}$=HIGH, $f_0=\overline{LEAB}$ =10 MHz, V_{IN}=3.4V or V_{IN}=GND	1.2	3.4	mA
		V_{CC}=Max., f_0=10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f_1=5 MHz, $\overline{CEAB}$ and $\overline{OEAB}$=LOW, $\overline{CEBA}$=HIGH, $f_0=\overline{LEAB}$ =10 MHz, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC}-0.2V$	2.8	5.6[13]	mA
		V_{CC}=Max., f_0=10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f_1=5 MHz, $\overline{CEAB}$ and $\overline{OEAB}$=LOW, $\overline{CEBA}$=HIGH, $f_0=\overline{LEAB}$ =10 MHz, V_{IN}=3.4V or V_{IN}=GND	5.1	14.6[13]	mA

Notes:
10. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.
11. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
12. I_C = $I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
    I_C = $I_{CC}+\Delta I_{CC}D_H N_T+I_{CCD}(f_0/2 + f_1 N_1)$
    I_{CC} = Quiescent Current with CMOS input levels
    ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
    D_H = Duty Cycle for TTL inputs HIGH

N_T = Number of TTL inputs at D_H
I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)
f_0 = Clock frequency for registered devices, otherwise zero
f_1 = Input signal frequency
N_1 = Number of inputs changing at f_1
All currents are in milliamps and all frequencies are in megahertz.
13. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

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Switching Characteristics Over the Operating Range

Parameter	Description	FCT2543T				FCT2543AT				Unit	Fig. No.[15]
		Military		Commercial		Military		Commercial			
		Min.[14]	Max.	Min.[14]	Max.	Min.[14]	Max.	Min.[14]	Max.		
tPLH tPHL	Propagation Delay Transparent Mode A to B or B to A	2.0	10.0	2.5	8.5	2.5	7.5	2.5	6.5	ns	1, 3
tPLH tPHL	Propagation Delay LEBA to A LEAB to B	2.5	14.0	2.5	12.5	2.5	9.0	2.5	8.0	ns	1, 5
tPZH tPZL	Output Enable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	14.0	2.0	12.0	2.0	10.0	2.0	9.0	ns	1, 7, 8
tPZH tPZL	Output Disable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	13.0	2.0	9.0	2.0	8.5	2.0	7.5	ns	1, 7, 8
tS	Set-Up Time HIGH or LOW, A or B to LEBA or LEAB	3.0		2.0		2.0		2.0		ns	9
tH	Hold Time HIGH or LOW, A or B to LEBA or LEAB	2.0		2.0		2.0		2.0		ns	9
tW	Pulse Width LOW LEBA or LEAB	5.0		5.0		5.0		5.0		ns	5

Parameter	Description	FCT2543CT				FCT2543DT		Unit	Fig. No.[15]
		Military		Commercial		Commercial			
		Min.[14]	Max.	Min.[14]	Max.	Min.[14]	Max.		
tPLH tPHL	Propagation Delay Transparent Mode A to B or B to A	2.5	6.1	2.5	5.5	1.5	4.4	ns	1, 3
tPLH tPHL	Propagation Delay LEBA to A, LEAB to B	2.5	8.0	2.5	7.0	1.5	5.0	ns	1, 5
tPZH tPZL	Output Enable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	9.0	2.0	8.0	1.5	5.4	ns	1, 7, 8
tPZH tPZL	Output Disable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	7.5	2.0	6.5	1.5	4.3	ns	1, 7, 8
tS	Set-Up Time HIGH or LOW, A or B to LEBA or LEAB	2.0		2.0		1.5		ns	9
tH	Hold Time HIGH or LOW, A or B to LEBA or LEAB	2.0		2.0		1.5		ns	9
tW	Pulse Width LOW LEBA or LEAB	5.0		5.0		3.0		ns	5

Shaded areas contain preliminary information.

Notes:
14. Minimum limits are guaranteed but not tested on Propagation Delays.
15. See "Parameter Measurement Information" in the General Information Section.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.4	CY74FCT2543DTQC	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2543DTSOC	S13	24-Lead (300-Mil) Molded SOIC	
5.3	CY74FCT2543CTPC	P13/13A	24-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT2543CTQC	Q13	24-Lead (150-Mil) QSOP	
	CY74FCT2543CTSOC	S13	24-Lead (300-Mil) Molded SOIC	
6.1	CY54FCT2543CTDMB	D14	24-Lead (300-Mil) CerDIP	Military
	CY54FCT2543CTLMB	L64	28-Square Leadless Chip Carrier	
6.5	CY74FCT2543ATPC	P13/13A	24-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT2543ATQC	Q13	24-Lead (150-Mil) QSOP	
	CY74FCT2543ATSOC	S13	24-Lead (300-Mil) Molded SOIC	
7.5	CY54FCT2543ATDMB	D14	24-Lead (300-Mil) CerDIP	Military
	CY54FCT2543ATLMB	L64	28-Square Leadless Chip Carrier	
8.5	CY74FCT2543TPC	P13/13A	24-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT2543TQC	Q13	24-Lead (150-Mil) QSOP	
	CY74FCT2543TSOC	S13	24-Lead (300-Mil) Molded SOIC	
10	CY54FCT2543TDMB	D14	24-Lead (300-Mil) CerDIP	Military
	CY54FCT2543TLMB	L64	28-Square Leadless Chip Carrier	

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